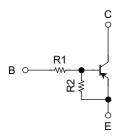
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

# RN2907FE, RN2908FE, RN2909FE

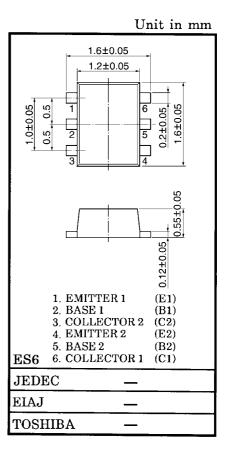
Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- Two devices are incorporated into an Extreme-Super-Mini (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.
   Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN1907FE~RN1909FE

### **Equivalent Circuit and Bias Resistor Values**



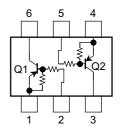
Type No.	R1 (kΩ)	R2 (kΩ)
RN2907FE	10	47
RN2908FE	22	47
RN2909FE	47	22



## Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage	RN2907FE~RN2909FE	$V_{CBO}$	-50	V	
Collector-emitter voltage	KNZ9071 E-KNZ9091 E	V <sub>CEO</sub>	-50	V	
	RN2907FE		-6	V	
Emitter-base voltage	RN2908FE	$V_{EBO}$	-7		
	RN2909FE		-15		
Collector current		Ic	-100	mA	
Collector power dissipation	RN2907FE~RN2909FE	P <sub>C</sub> (Note)	100	mW	
Junction temperature	KINZ907FE~KINZ909FE	Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

# Equivalent Circuit (top view)



Note: Total rating

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TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general
can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the
buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and
to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or
damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.

• The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.



#### Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2907FE~2909FE	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-100	nA
		I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$	_	_	-500	IIA
Emitter cut-off current	RN2907FE	I <sub>EBO</sub>	$V_{EB} = -6 \text{ V}, I_C = 0$	-0.081	_	-0.15	mA
	RN2908FE		$V_{EB} = -7 \text{ V}, I_{C} = 0$	-0.078	_	-0.145	
	RN2909FE		$V_{EB} = -15 \text{ V}, I_C = 0$	-0.167	_	-0.311	
	RN2907FE	h <sub>FE</sub>	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -10 mA	80	_	_	
DC current gain	RN2908FE			80	_	_	
	RN2909FE			70	_	_	
Collector-emitter saturation voltage	RN2907FE~2909FE	V <sub>CE (sat)</sub>	$I_C = -5 \text{ mA},$ $I_B = -0.25 \text{ mA}$	_	-0.1	-0.3	٧
Input voltage (ON)	RN2907FE	V <sub>I (ON)</sub>	$V_{CE} = -0.2 \text{ V},$ $I_{C} = -5 \text{ mA}$	-0.7	_	-1.8	V
	RN2908FE			-1.0	_	-2.6	
	RN2909FE			-2.2	_	-5.8	
Input voltage (OFF)	RN2907FE	V <sub>I (OFF)</sub>	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -0.1 mA	-0.5	_	-1.0	V
	RN2908FE			-0.6	_	-1.16	
	RN2909FE			-1.5	_	-2.6	
Transition frequency	RN2907FE~2909FE	f <sub>T</sub>	$V_{CE} = -10 \text{ V},$ $I_{C} = -5 \text{ mA}$	_	200	_	MHz
Collector output capacitance	RN2907FE~2909FE	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0,$ f = 1 MHz	_	3	6	pF
Input resistor	RN2907FE	R1	_	7	10	13	
	RN2908FE			15.4	22	28.6	kΩ
	RN2909FE			32.9	47	61.1	
Resistor ratio	RN2907FE	R1/R2	_	0.191	0.213	0.232	
	RN2908FE			0.421	0.468	0.515	
	RN2909FE			1.92	2.14	2.35	

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The information contained herein is subject to change without notice.

Type Name	Marking
RN2907FE	Type name
RN2908FE	Type name
RN2909FE	Type name